

Engineering Framework for Scalable Quantum Device Manufacturing-Ver.1.0

I. Technology-Agnostic Foundation

A. Theoretical Limits & Modeling

This layer defines universal requirements for coherence, error thresholds, and modeling, applicable across qubit technologies. It forms the basis for deriving general engineering rules.

Step	Description
Quantum Mechanical Limits	Define coherence times (T_1 , T_2), noise sources, and gate fidelity ($<10^{-3}$).
Fault Tolerance Requirements	Select QEC (surface code, LDPC, etc.) and calculate physical-to-logical qubit ratio.
Thermodynamic Constraints	Understand temperature and energy constraints per platform (e.g., mK for superconductors).
Electromagnetic Modeling	Simulate resonator-QED coupling, Schrödinger-Poisson interactions, etc.
Dimensionality & Embedding	Choose geometry (1D, 2D, 3D) and coupling (bus, nearest-neighbor).

B. General Engineering Process Flow

This defines the fabrication-agnostic methodology: from material selection to qubit layout and integration of classical control systems.

- Material Selection: Physical property-based selection (e.g., bandgap, conductivity, SOC).
- Material Processing & Deposition: Use ALD, CVD, sputtering, etc., to fabricate layers.
- Annotation & Embedding: Logical qubit boundaries, couplers, gates, and interfaces are marked.
- Interface & Transducer Integration: Connect classical and quantum layers using tunable gates, optical cavities, etc.
- Quality Control: Use SEM, AFM, cryogenic testing for structural and electrical verification.

II. Device-Specific Implementations

Branching into specific technologies from the general framework.

- Superconducting Qubits: Use Nb/Al, implement TSVs, tunable Josephson junctions.
- Topological Qubits: Employ MZMs, TIs, braiding logic. Layout for error-immune computation.
- Spin Qubits: Quantum dots in ²⁸Si or NV centers in diamond. Long coherence at small size.
- Trapped Ions: Optical lattice-based logic, requires vacuum and laser control.

III. Result Tabulation and Reporting Schema

Use this reporting format to record test outcomes and benchmark against platform-independent targets.

Module	Metric	Method	Target/Range	Notes
Materials	Surface roughness (nm)	AFM, SEM	<0.5 nm	All devices
Qubit Quality	T ₁ , T ₂ (μs)	Ramsey, Hahn echo	>100 μs	Surface code compatible
Interface	Gate tunability (GHz/V)	Spectroscopy	0.1–1 GHz/V	Gatemons, charge qubits
Control Lines	Crosstalk (%)	RF injection + mapping	<1%	All platforms
Yield	Working qubits/wafer	Electrical + fidelity test	>80%	Based on logical mapping
Error Rate	Gate/Readout error (%)	RB / Fidelity tests	<0.1%	Fault-tolerance threshold

IV. Use of AI, Simulation, and HPC

Advanced computational tools can enhance material analysis, fault prediction, and layout optimization.

- AI/ML: Defect classification, junction prediction using CV and RL models.
- Quantum Simulation: Test coherence, error tolerance in digital/analog simulators pre-fabrication.
- Digital Twins: Full-stack performance model combining error models, layout, and EM effects.
- Multi-physics Solvers: Simulate thermal, electric, and quantum behavior (e.g., COMSOL, Ansys).

Visual Block Diagram: Quantum Device Engineering Framework

